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(54) Title: LASER LIFT-OFF PROCESSING SYSTEM INCLUDING METAL GRID

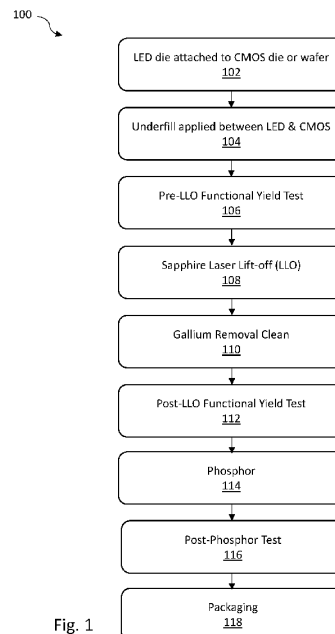


Fig. 1

(57) Abstract: A method of manufacturing a light emitting diode (LED) device includes forming an LED structure by depositing a plurality of semiconductor layers on a transparent substrate. Trenched metal is placed in the plurality of semiconductor layers, with the trenched metal contacting the transparent substrate. The LED structure is attached to a CMOS structure with electrical interconnects that define a cavity therebetween. Laser light is used to provide laser lift-off of the transparent substrate from the plurality of semiconductor layers.

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